

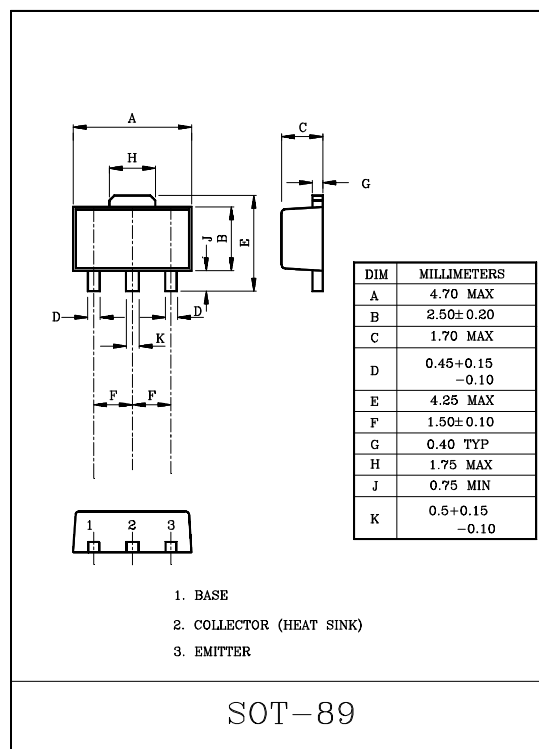
HIGH CURRENT APPLICATION.

FEATURES

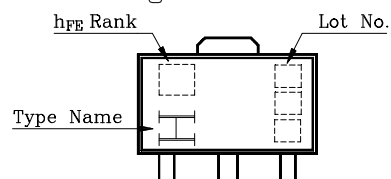
- 1W (Mounted on Ceramic Substrate).
- Small Flat Package.
- Complementary to KTC4375.

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-30	V
Collector-Emitter Voltage	V_{CEO}	-30	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-1.5	A
Base Current	I_B	-0.3	A
Collector Power Dissipation	P_C	500	mW
	P_{C^*}	1	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~150	$^\circ\text{C}$

 P_{C^*} :KTA1663 mounted on ceramic substrate(250mm²x0.8t)

Marking

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=-30\text{V}, I_E=0$	-	-	-100	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=-5\text{V}, I_C=0$	-	-	-100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=-10\text{mA}, I_B=0$	-30	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=-1\text{mA}, I_C=0$	-5.0	-	-	V
DC Current Gain	$h_{FE}(\text{Note})$	$V_{CE}=-2\text{V}, I_C=-500\text{mA}$	100	-	320	
Collector-Emitter Saturation Voltage	$V_{CE(\text{sat})}$	$I_C=-1.5\text{A}, I_B=-0.03\text{A}$	-	-	-2.0	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=-2\text{V}, I_C=-500\text{mA}$	-	-	-1.0	V
Transition Frequency	f_T	$V_{CE}=-2\text{V}, I_C=-500\text{mA}$	-	120	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$	-	-	50	pF

Note : h_{FE} Classification O:100~200 , Y:160~320

